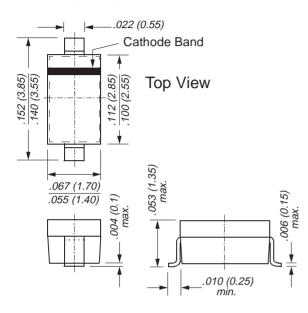


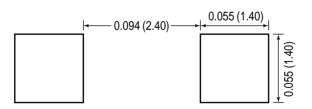
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Tuner Diodes

SOD-123 (BB721)



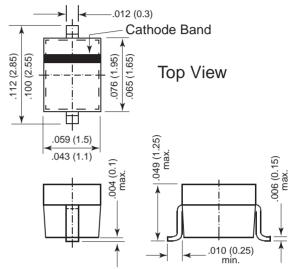
Mounting Pad Layout SOD-123 (BB721)



Features

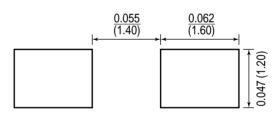
- Silicon epitaxial planar capacitance diodes with very wide effective capacitance variation for tuning the whole range of UHF television bands.
- Two BB721/BB721S tuner diodes in series are used for direct satellite receivers.
- These diodes are available as singles or as matched sets of two or more units according to the tracking condition described in the table of characteristics.

SOD-323 (BB721S)



Dimensions in inches and (millimeters)

Mounting Pad Layout SOD-323 (BB721S)



Mechanical Data

Case: BB721 = SOD-123 Plastic Case BB721S = SOD-323 Plastic Case

Weight: BB721 = approx. 0.01g BB721S = approx. 0.004g

Packaging Codes/Options:

SOD-123: D3/10K per 13" reel (8mm tape), 30K/box D4/3K per 7" reel (8mm tape), 30K/box SOD-323: D5/10K per 13" reel (8mm tape), 30K/box D6/3K per 7" reel (8mm tape), 30K/box

Maximum Ratings and Thermal Characteristics (Tc = 25°C unless otherwise noted)

| Parameter | Symbol | Value | Unit V | |
|---------------------------|--------|-------------|-----------|--|
| Reverse Voltage | VR | 32 | | |
| Junction Temperature | TJ | 125 | °C | |
| Storage Temperature Range | Ts | -55 to +125 | °C | |

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Electrical Characteristics (Tc = 25°C unless otherwise noted)

| Parameter | Symbol | Min | Тур | Max | Unit |
|--|--------------------------------------|---------------------|-----|-----------------------|------|
| Reverse Breakdown Voltage at I _R = 100μΑ | V _{(BR)R} | 32 | _ | _ | V |
| Leakage Current at V _R = 30V | IR | - | - | 10 | nA |
| Capacitance f = $1MH_Z$ at $V_R = 28V$ at $V_R = 25V$ at $V_R = 2V$ | Ctot | 1.9 2.1 14.01 | _ | 2.29 2.39 16.33 | pF |
| Effective Capacitance Ratio $f = 1MHz$ at $V_R = 1$ to 28V | <u>Ctot (1V)</u> Ctot (28V) | 8 | _ | _ | _ |
| at $V_R = 2$ to 25V | $\frac{C_{tot} (2V)}{C_{tot} (25V)}$ | 5.86 | _ | 7.78 | - |
| Series Resistance at f = 470 MHz, Ctot = 14 pF | rs | _ | _ | 0.8 | Ω |
| Series Inductance | Ls | _ | 2.5 | _ | nH |

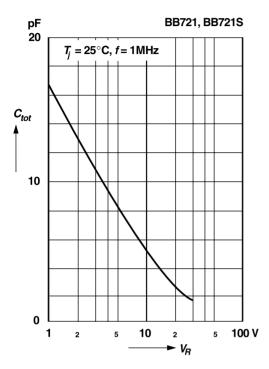
For any two of six consecutive diodes in the carrier tape, the maximum capacitance deviation in the reverse bias voltage of VR = 0.5 to 28V is 3%



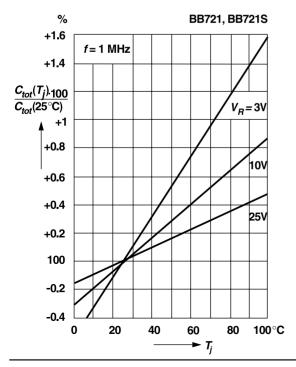
Ratings and Characteristic Curves (TA = 25°C unless otherwise noted)

Capacitance

versus reverse voltage



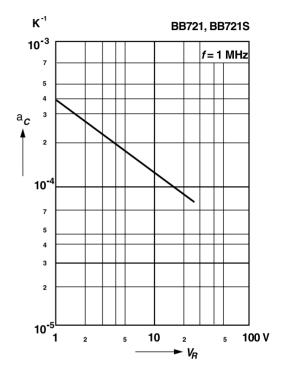
Relative capacitance versus junction temperature



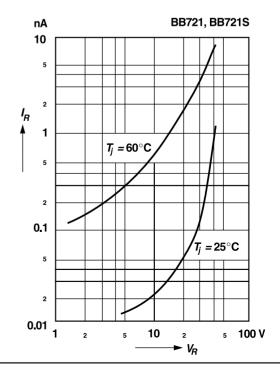
Temperature coefficient of capacitance versus reverse voltage

BB721 and BB721S

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Leakage current versus reverse voltage



Document Number 88155 15-May-02

BB721 and BB721S

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Ratings and

Characteristic Curves (TA = 25°C unless otherwise noted)

Q-Factor

versus frequency

